Establishing a Ti-Cu-Pt-Au Thin Film Conductor on Low-Temperature, Co-Fired Ceramic (LTCC) for High Temperature Electronics

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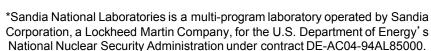
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National Security Complex Kansas City, MO

Acknowledgement: Thee authors wish to and **Brian Wroblewski** for his thorough review of the proceedings.







The development and operational sustainment of down hole renewable (geothermal) and non-renewable (fossil fuel) energy resources will be subjected to increasingly higher costs factors:

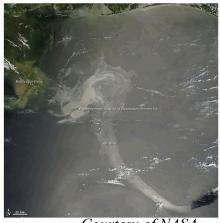


Courtesy of Dept. of Energy



Courtesy of Dept. of Energy

Site operations (\$M/day)



Courtesy of NASA

Liability (\$B)

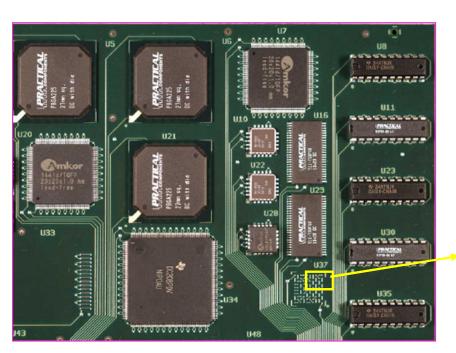
Site preparation (\$B)

- Placing sensor electronics directly down hole can significantly improve both the efficiency and the reliability of well production.
- Oil, gas, and geothermal wells present some of the harshest service conditions for electronics and electrical equipment.
 - Temperatures: 300°C continuous; 350°C peak
 - Pressures: 15,000 to 30,000 psi
 - Vibration: PDS (g²/Hz), 0.01 0.1 (0.6 3 kHz)
 - Corrosion: H₂S and H₂ gas, brine, and superheated steam.

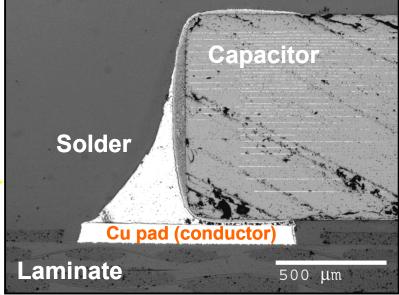


Courtesy of Sandia National Labs.

 Electronic packaging is becoming the enabling technology for high temperature electronic systems.

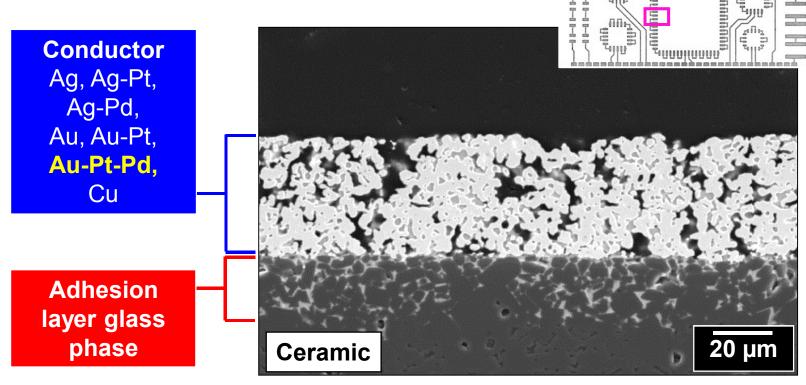




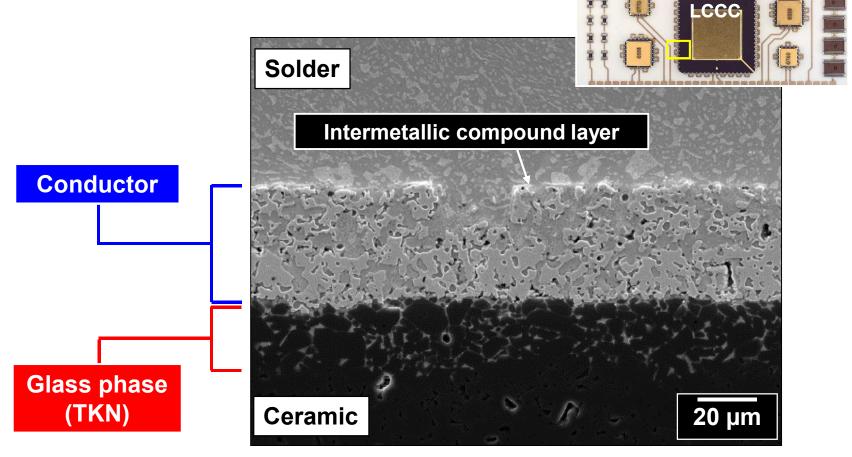


 Organic laminate technologies are reaching their mechanical and temperature limitations under such operating conditions.

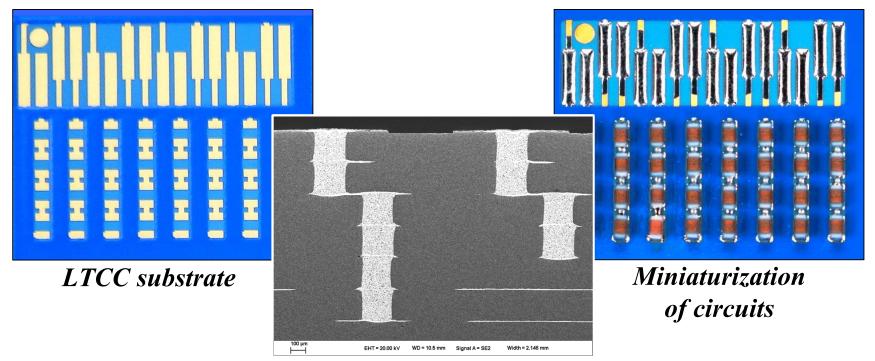
- Ceramic substrates have the capacity to extend the operational range of electronics into down-hole applications.
- <u>Hybrid Microcircuit</u> (HMC) assemblies are based on an alumina ceramic substrate and *fired* thick film (conductor) circuit.



The molten solder wets to, and penetrates the pores of, the thick film layer to form the interconnection.

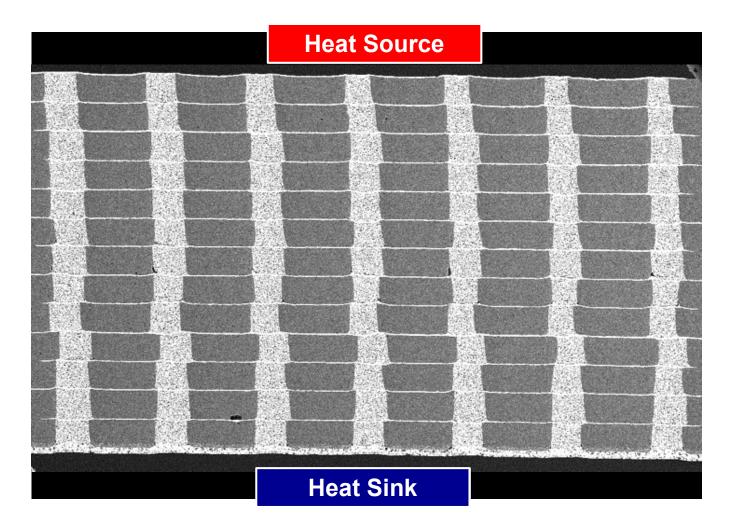


- The development of low-temperature, co-fired ceramic (LTCC) substrates provided the same multi-layer capability enjoyed by organic laminates.
 - Layer-by-layer, build-up technology places internal traces and vias into the LTCC substrate that can create highly complex circuits.

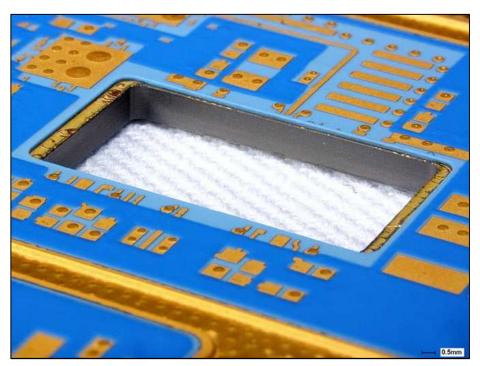


Signal traces and vias

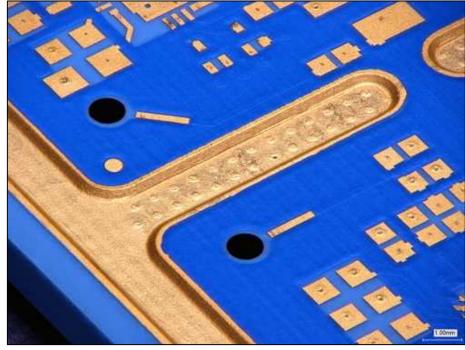
♦ Special via-plus-trace designs can optimize thermal management.



◆ The LTCC build-up technology also allows for the creation of three-dimensional structures such as windows and cavities.

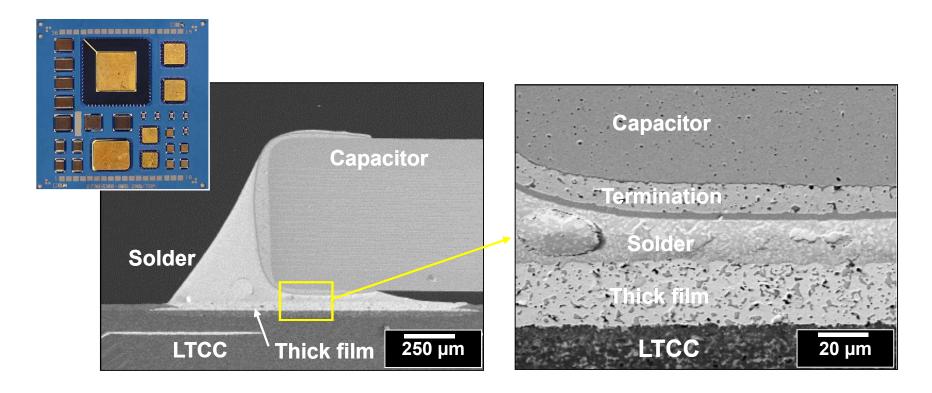


Window



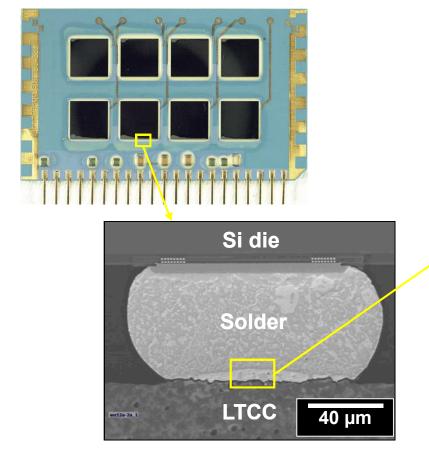
Cavity

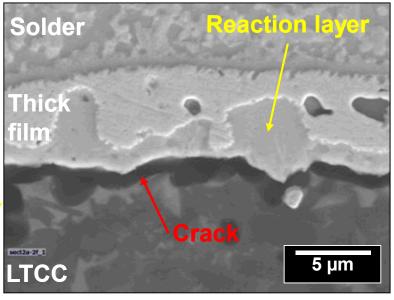
 The early development of HMC that incorporated LTCC, and numerous applications today, use thick film conductors.



 Although such circuits could be very complex, "lines-and-spaces" did not pose particularly demanding requirements.

 However, the miniaturization required by multi-chip modules (MCMs) pushed the limits of thick film conductor technology.







Unexpected material reactions can degrade the long-term reliability of the solder joints.

The next step to improve functionality and miniaturization was replacing thick film conductors with thin film technology.

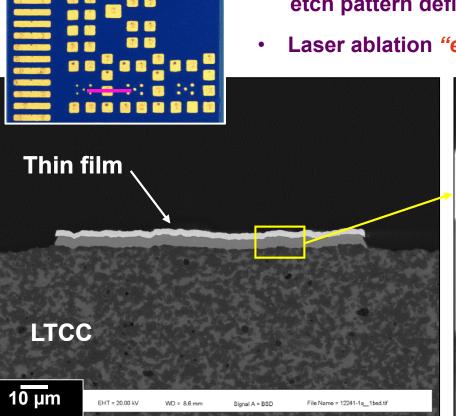
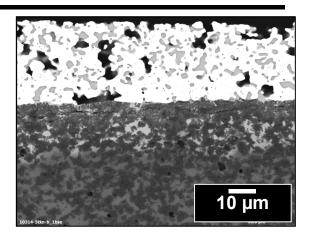
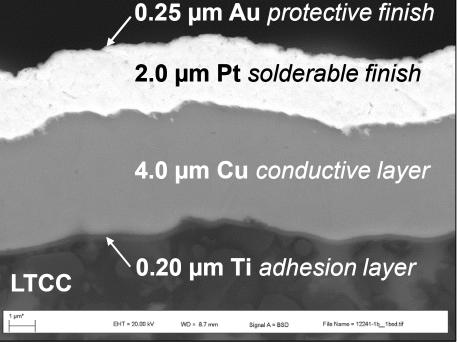


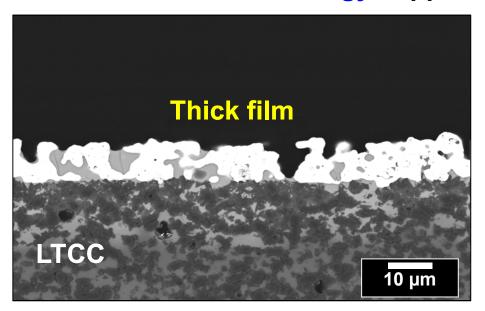
Photo imaging/plasma etch pattern definition

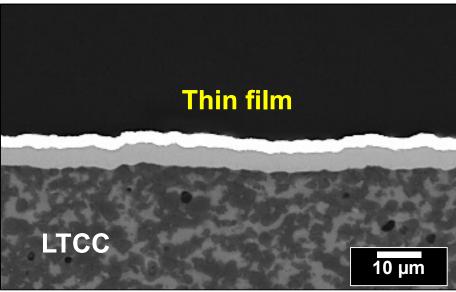
Laser ablation "erasing"

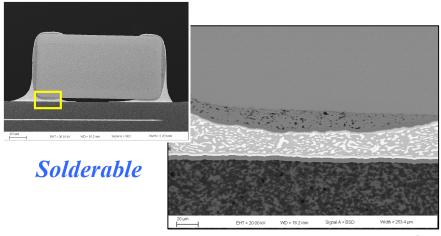




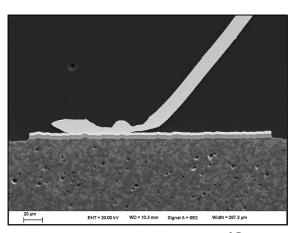
◆ The thin film technology supports critical functional capabilities:







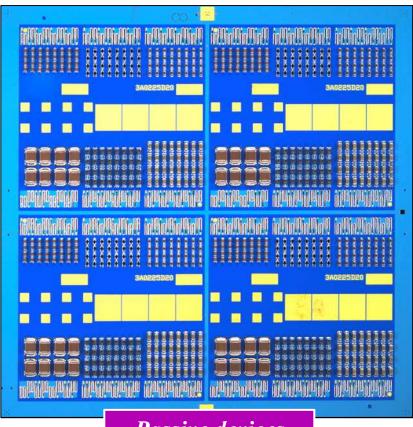
Wire and ribbon bondable



The LTCC-based, HMC technology using thin film conductors is illustrated by these accelerated aging test vehicles that readily incorporates 1.0 mm BGAs and 0402 passive devices.







Passive devices

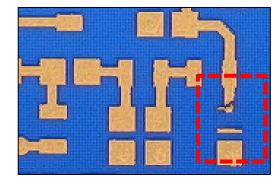
Path-Forward

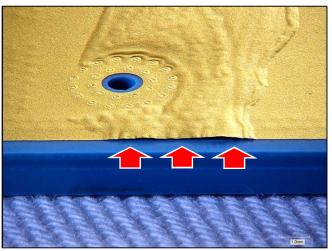
Problem:

Thin film performance and reliability are sensitive to numerous factors:

- Choice of layers (the "stack")
- Interphase adhesion
- Surface contamination

The potentially significant impact on product yield necessitates a means to identify root-cause from amongst multiple contributing factors.

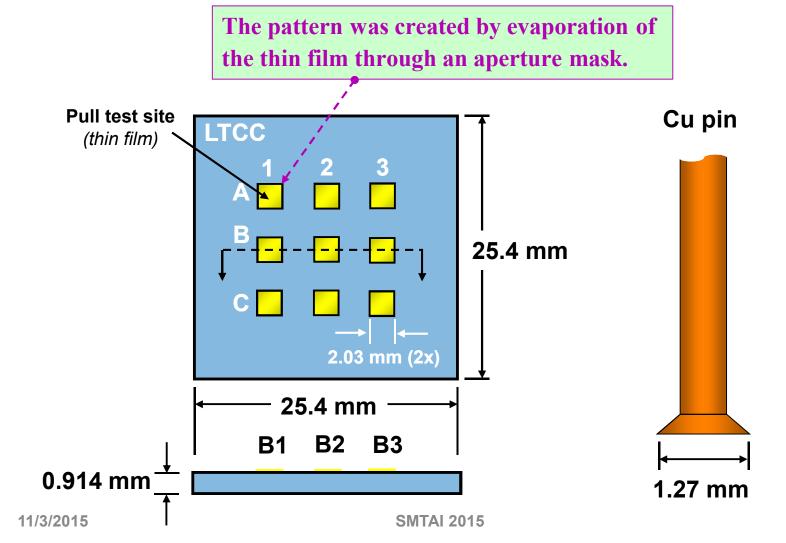




Objective:

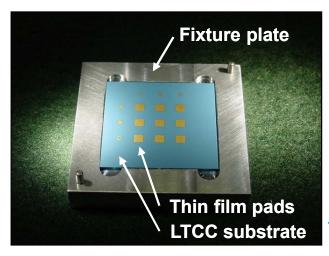
Product optimization required a means to assess, at a more basic level, the strength of solder joints made to thin films on LTCC.

◆ A pin pull test was developed to measure the tensile strength of solder joints made to thin film conductors on LTCC substrates.

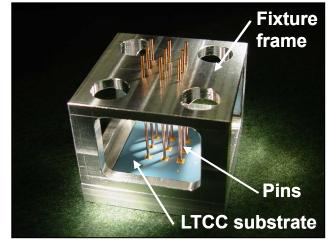


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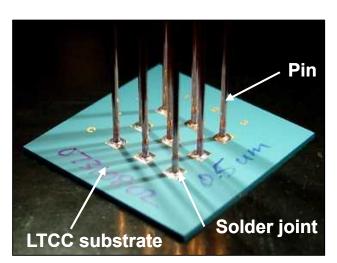
◆ The test assembly was fabricated by soldering a pin to each of the nine (9) thin film pads, using a conduction furnace.



Substrate is placed on the fixture plate.



Fixture frame and pins are put into place.

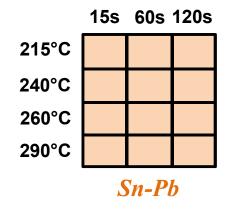


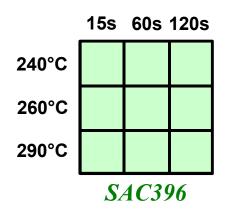
Completed test specimen

- ◆ The low-temperature, co-fired ceramic (LTCC) substrate is fabricated from the DuPont™ 951 tape*
- ♦ The thin film is ... 0.20 Ti 4.0 Cu 2.0 Pt 0.25 Au (μm)
- ♦ The solder alloys (wt.%) ... 63Sn-37Pb (Sn-Pb)

... 95.5Sn-3.9Ag-0.6Cu (SAC396)

Soldering times (seconds) and temperatures (°C):





^{*} $DuPont^{TM}$ is a registered trademark of E.I. DuPont de Nemours Corp., Wilmington, DE.

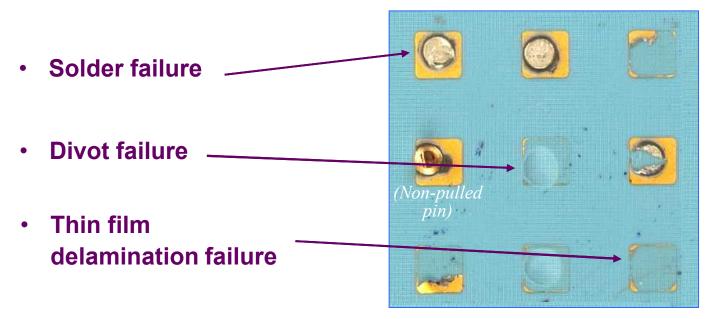
◆ The role of solid-state aging was evaluated for the Sn-Pb joints.

◆ The test samples were assembled using the two limiting cases of process variables ... 215°C, 15s
... 290°C, 120s

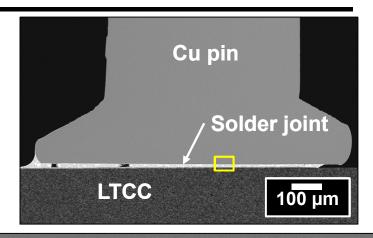
Solid-state aging times (days) and temperatures (°C):

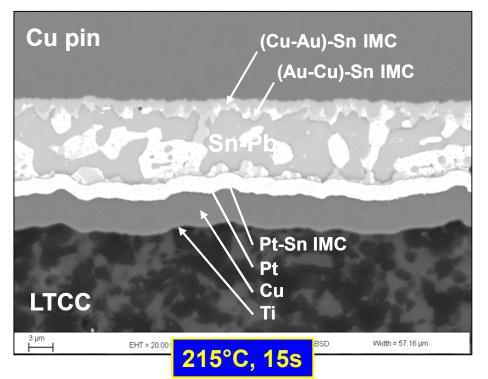


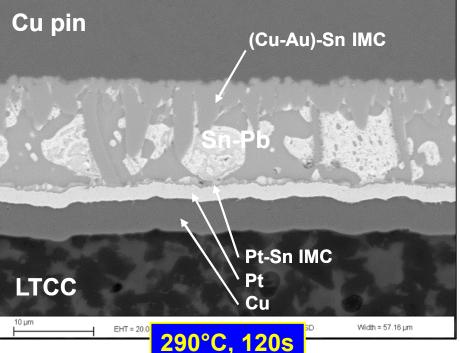
- The pin pull test was performed at 10 mm/min.
- ◆ Eight (8) of nine (9) pins were pull tested on duplicate test specimens per condition, for a total of sixteen (16) data points.
- Fracture mode analysis is a critical step in this analysis.
 - There were three predominant failure modes:



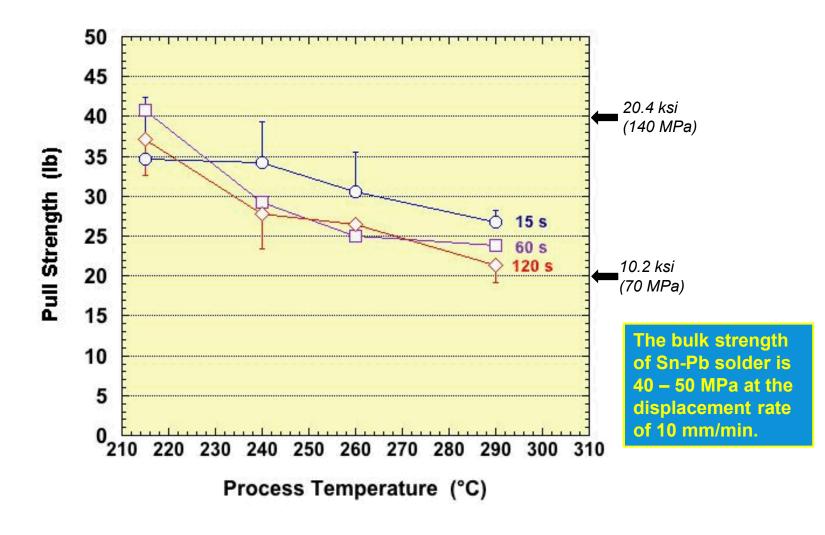
- ◆ The solder joint microstructures are shown for the Sn-Pb solder.
 - Very minimal reaction between the Sn-Pb solder and Pt solderable layer.
 - Significant IMC reactions occurred at the Sn-Pb / Cu pin interface.



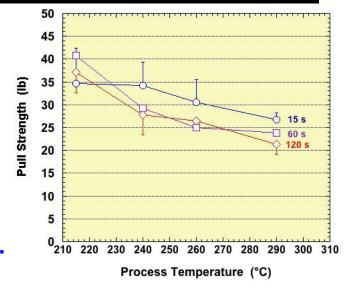


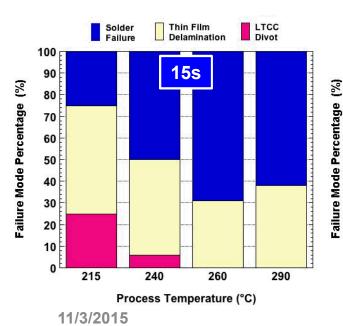


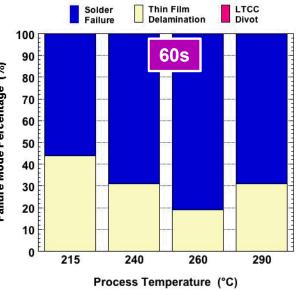
The Sn-Pb solder pin pull test data are shown in this plot.



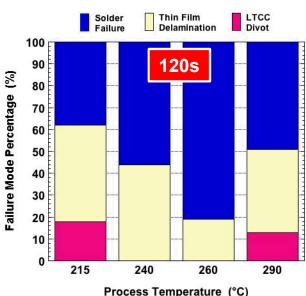
- The Sn-Pb solder failure mode data are shown for the three process times.
 - 215 260°C: Increasing the process temperature caused delamination and divot failure modes to be replaced with solder failures.
 - 290°C: The trend showed a slight reversal.





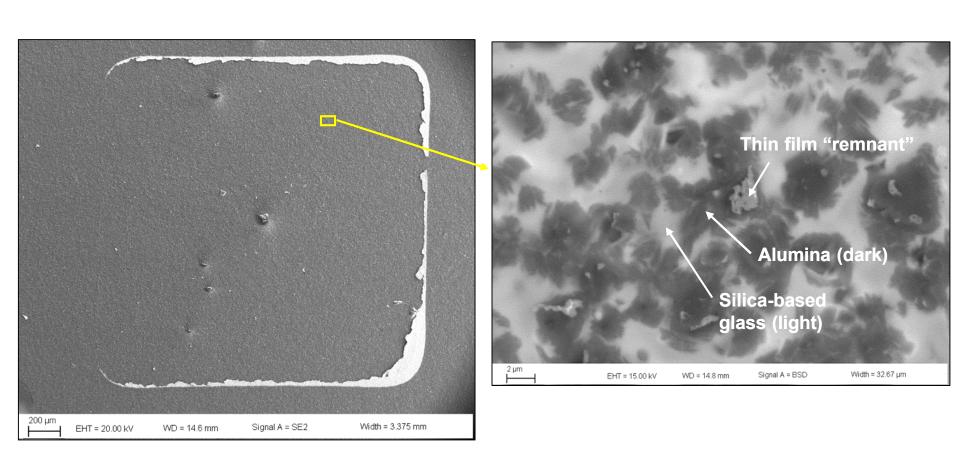


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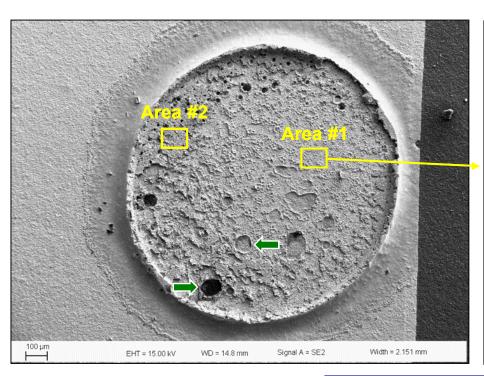
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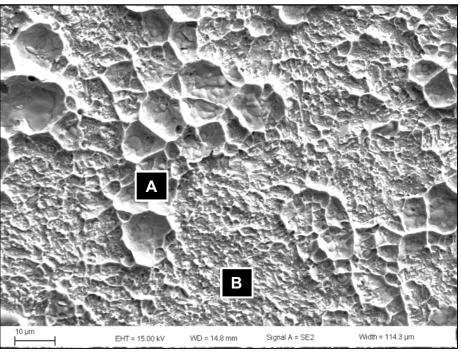
◆ The thin film delamination failure mode was characterized by separation at the *immediate* Ti adhesion layer / LTCC interface.



Sn-Pb solder; 215°C, 15s

The solder failure mode exhibited multiple crack paths.



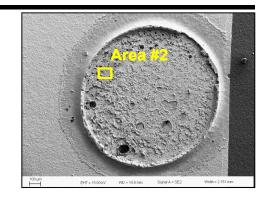


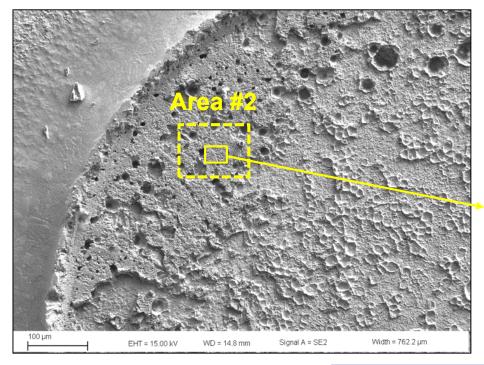
Sn-Pb solder; 215°C, 15s

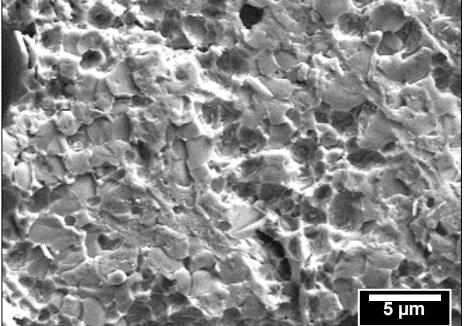
- Green arrows ... minor voids
- Two fracture morphologies indicated by areas #1 and #2.

- Area #1:
 - "A" ... ductile failure in the solder
 - "B" ... Pt/Pt-Sn IMC interface failure

- ♦ The area #2 morphology is examined, below.
 - Fracture surface ... brittle, intergranular
 - EDX analysis ... high-Au, (Au-Cu)-Sn IMC that formed at the solder / Cu pin interface.

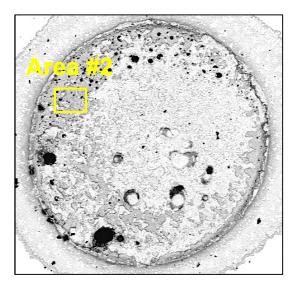




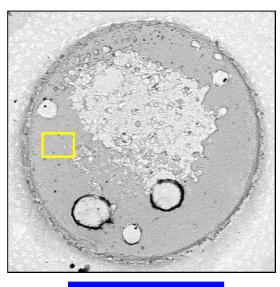


Sn-Pb solder; 215°C, 15s

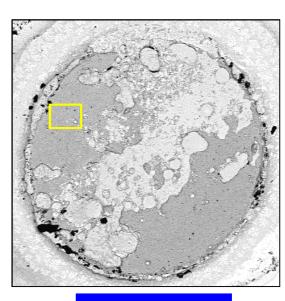
The fracture surface changed with process parameter "severity."



215°C, 15s



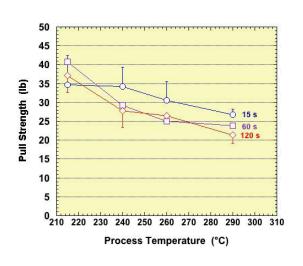
260°C, 60s



290°C, 120s

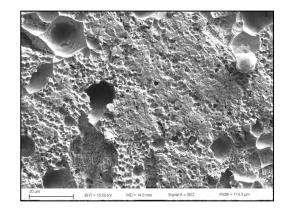
- The area #2 fracture surface increased with "severity."
- ◆ The area #2 fracture surfaces of 260°C, 60s and 290°C, 120s progressed through the low-Au, (Cu-Au)-Sn IMC.

An analysis was made, based on all three data sources:



Solder Thin Film Delamination Divot

The Failure Delamination



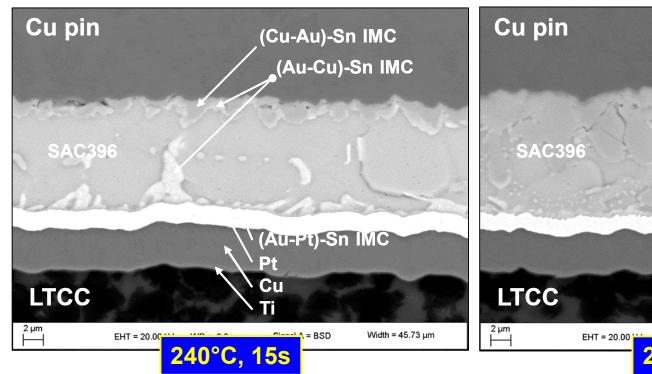
Pull strength

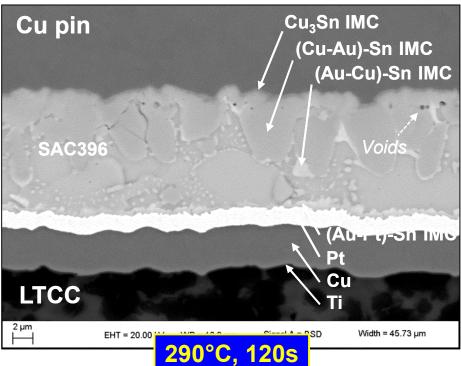
Failure mode analysis

Fracture morphology

- All joint strengths exceeded that of the bulk solder.
- The strength loss with soldering time and temperature was correlated to an increase of the solder failure mode.
- Increased solder failure mode was accompanied by an increased fracture path along the IMC at the solder/Cu pin interface.
- The increased presence of Au in the IMC layer decreased the intrinsic strength of the Cu/IMC interface with increased process "severity".

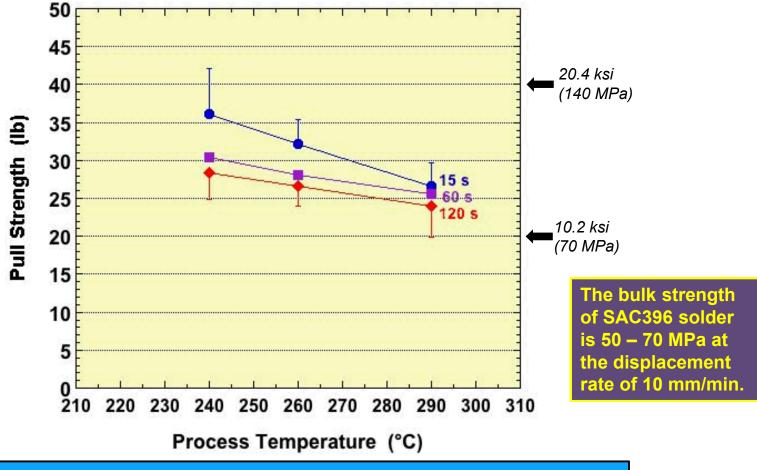
◆ The SAC396 samples were examined versus the soldering process.





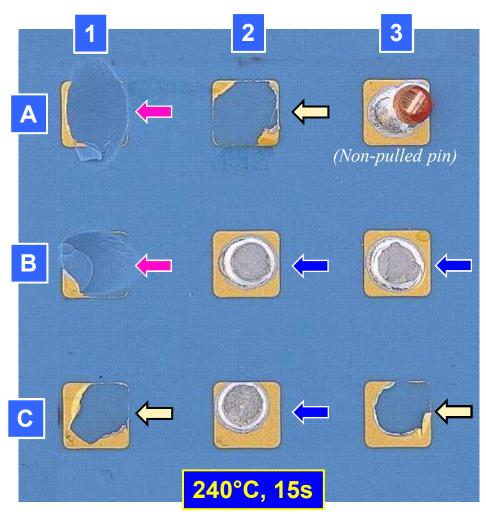
- ♦ The SAC396 joints had slightly different interface microstructures.
 - SAC396 retained Au more so in both interface IMC phases.
 - At 290°C, 120s, the SAC396 exhibited the Cu₃Sn phase at the solder / Cu pin interface.

The SAC396 solder joint strength is shown, below.

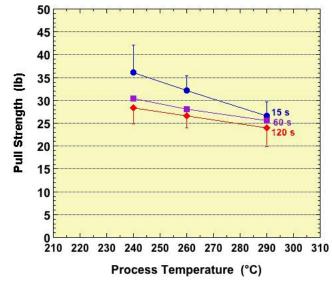


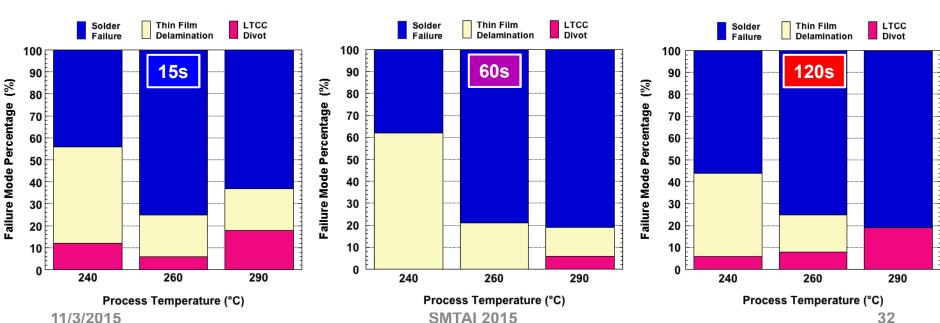
The strength magnitudes and trends replicated those of the Sn-Pb solder joints over the same temperature range.

- ◆ The SAC396 solder joints exhibited the same failure modes as were observed with the Sn-Pb samples.
 - Yellow arrows indicate thin film delamination.
 - Blue arrows indicate solder failure.
 - Magenta arrows indicate divot failure.

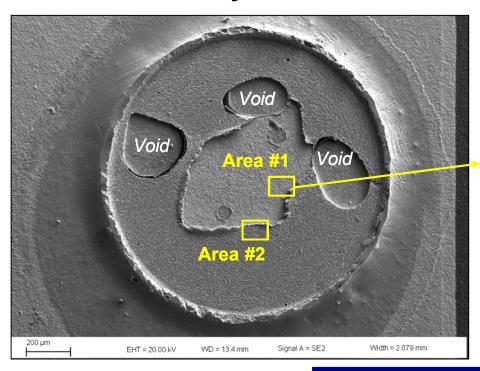


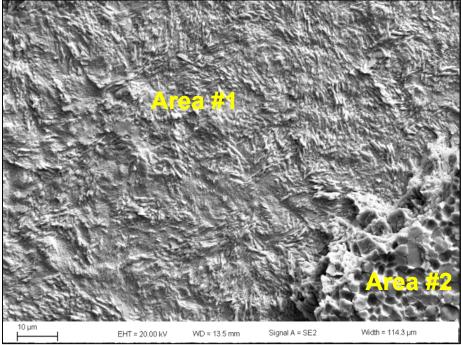
- The SAC396 solder failure mode data are shown for the three process times.
 - 240 290°C: Increasing the process temperature caused delamination and divot failure modes to be replaced with solder failures.
 - There is a persistent presence of the divot failure mode, particularly for 15s and 120s





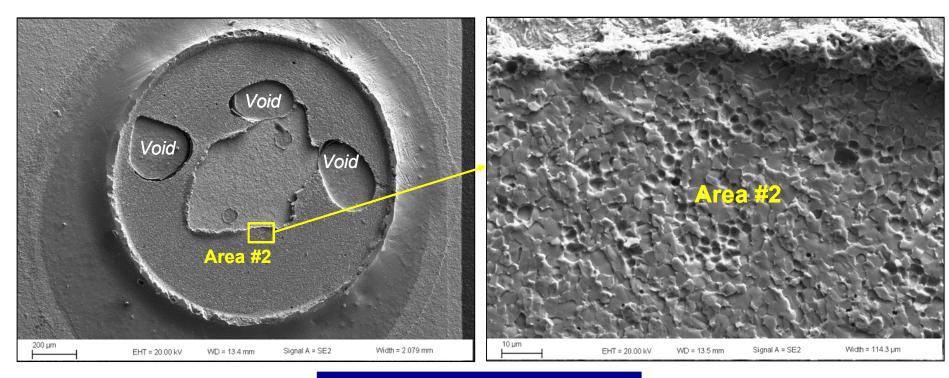
- The thin film delamination and divot failure mode morphologies were similar to those of the Sn-Pb solder.
- ◆ The SAC396 solder failure mode was examined more closely.
- ◆ The EDX analysis indicated area #1 as the Pt/Pt-Sn IMC interface.





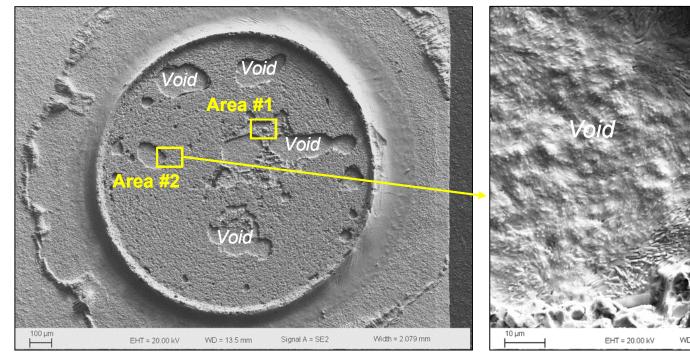
SAC396 solder; 240°C, 15s

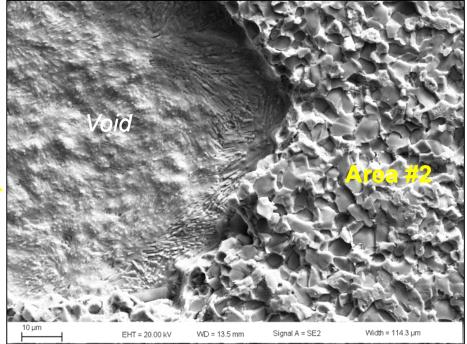
- ◆ The area #2 fracture surface had a brittle, intergranular morphology.
- ◆ The EDX analysis confirmed that the area #2 crack path passed through the *low-Au*, (Cu-Au)-Sn IMC layer.



SAC396 solder; 240°C, 15s

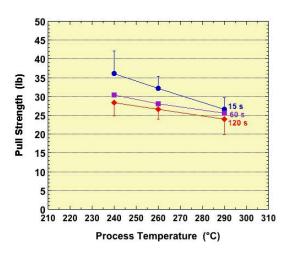
- ◆ The more severe process parameters caused an increase in the area #2 fracture morphology, after taking the voids into account.
- ◆ Interestingly, EDX analysis indicated that the area #2 crack path favored the low-Au, (Cu-Au)-Sn IMC layer.





SAC396 solder; 290°C, 120s

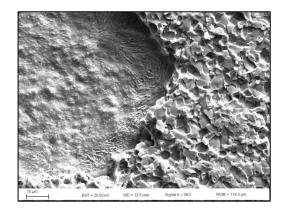
An analysis was made, based on all three data sources:



Solder Failure Delamination Divot

100
90
40
30
100
240
260
290

Process Temperature (°C)



Pull strength

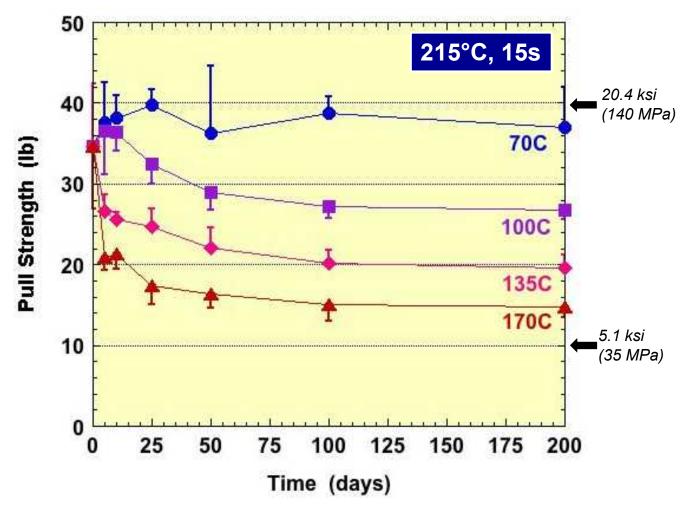
Failure mode analysis

Fracture morphology

- All joint strengths exceeded that of the bulk solder.
- The strength loss with soldering time and temperature was correlated to an increase of the solder failure mode.
- Increased solder failure mode was accompanied by an increased fracture path along the (Cu-Au)-Sn IMC at the solder/Cu pin interface.
- The divot failure mode maintained a presence, the cause of which were higher CTE mismatch residual stresses generated in the LTCC bulk.

Results – Solid State Aging, Sn-Pb Solder Joints

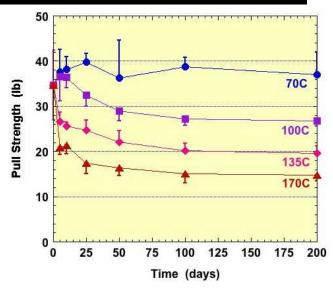
The Sn-Pb solder joints processed at 215°C for 15s experienced a loss of pull strength with an increase of solid-state aging.

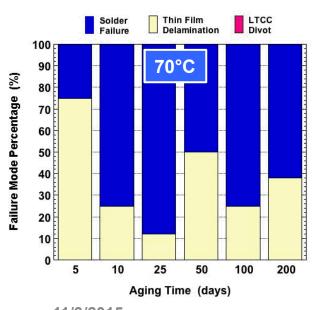


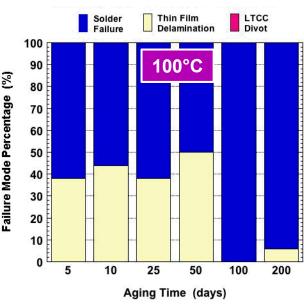
Results - Solid State Aging, Sn-Pb Solder Joints

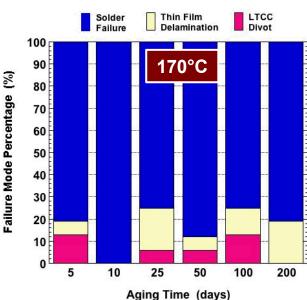
The pull strength data were correlated to the failure modes:

- Solder failure mode increased with the severity of aging at the expense of the delamination failure mode.
- Divot failure mode appeared in the 135°C and 170°C data, albeit, at low percentages.







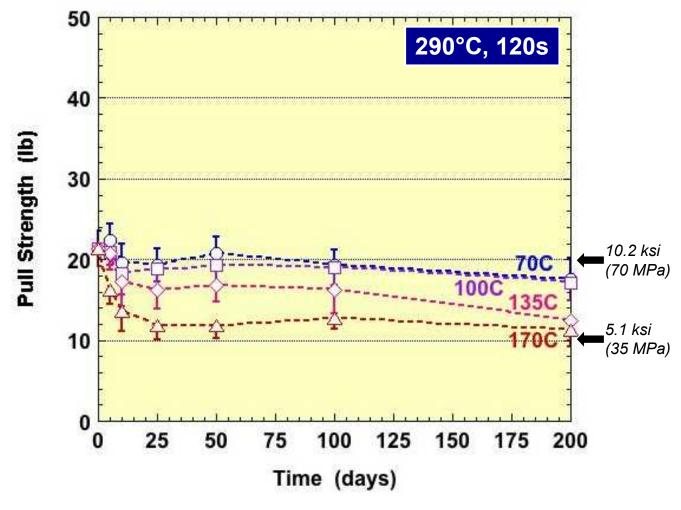


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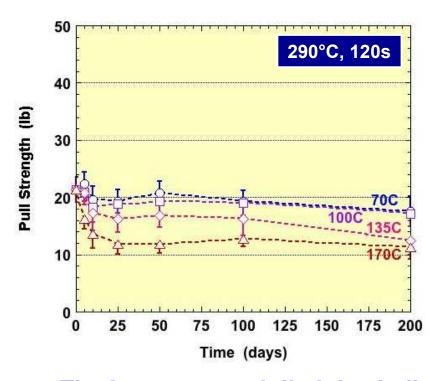
Results – Solid State Aging, Sn-Pb Solder Joints

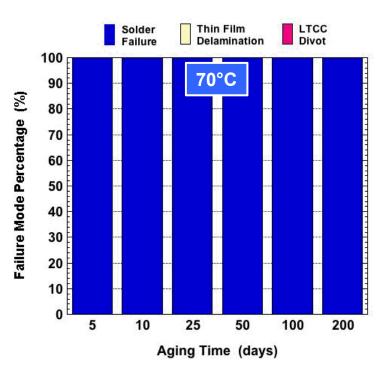
 The Sn-Pb solder joints processed at 290°C for 120s experienced a loss of pull strength with an increase of solid-state aging.



Results - Solid State Aging, Sn-Pb Solder Joints

The fracture sites exhibited exclusively, or nearly so, the solder failure mode for all aging temperatures and time durations.





- The lower strength limit is similar between [215°C, 15s] and [290°C, 120s].
- The more severe process conditions "collapsed," more effectively, the pull strengths following solid-state aging.

Summary

- A study was performed to evaluate the tensile strength of Sn-Pb and SAC396 solder joints made to 0.20Ti-4.0Cu-2.0Pt-0.25Au (μm) thin films on low-temperature, co-fired ceramic (LTCC) substrates.
- ◆ The strength performance was evaluated as a function of process (soldering) parameters for both Sn-Pb and SAC396 solder joints.
- ◆ The Sn-Pb joint strengths were also assessed as a function of solid-state aging (70 – 170° C; 5 – 200 days).
- ♦ Both solders exhibited similar pull strengths as well as the same strength loss with increased severity of the process parameters.
 - All strength magnitudes were more-than-adequate to meet the needs of engineering applications.
 - The strength loss was attributed in both cases to an increase in the solder failure mode specifically, the (Cu-Au)-Sn IMC layer.

Summary

- The solid-state aging caused the Sn-Pb solder joints to exhibit a loss of pull strength with increased temperature and time.
 - However, the strength loss was sensitive to the process (soldering) parameters.
 - It appeared that the harsher process parameters <u>accelerated</u>, rather than superimposed upon, the effects of solid-state aging.
- The explicit effect had by the Ti-Cu-Pt-Au thin film in the strength of the Sn-Pb and SAC396 solder joints included these factors:
 - The role of Au in the IMC formation.
 - The thin film delamination failure mode that predominated the high pull strengths.
 - Formation of the Pt-Sn IMC layer observed after solid-state aging ... stay tuned !!!